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In the Claims:

Amend the claim set, without prejudice, as detailed in the following complete listing of all claims (1 to 11):

Sb C 3
B1

1. (Currently amended) A method of manufacturing an integrated circuit carrier, the method including the steps of providing a substrate; demarcating at least one receiving zone for an integrated circuit on the substrate and a plurality of island-defining portions arranged about said at least one receiving zone; and creating rigidity-reducing arrangements a serpentine member between neighboring island-defining portions by removing material from the substrate, thereby reducing thermal strains involving the said island-defining portions.
2. (Original) The method of claim 1 which includes forming electrical contacts in said at least one receiving zone and forming an electrical terminal in each island-defining portion, each electrical terminal being electrically connected via a track of a circuitry layer to one of the electrical contacts.
3. (Original) The method of claim 2 which includes forming the circuitry layer on a surface of the substrate by depositing a metal layer on the substrate.
4. (Cancelled)
5. (Cancelled)
6. (Previously amended) The method of claim 1 which includes creating the rigidity-reducing arrangements by etching through the substrate.
7. (Original) The method of claim 1 which includes forming the substrate from a wafer of undoped silicon having an insulating layer.

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8. (Original) The method of claim 1 which includes demarcating said at least one receiving zone by forming a recess in the substrate.
9. (Original) The method of claim 8 which includes forming the recess by etching the substrate.
10. (Cancelled)
11. (Cancelled)

B)

concluded